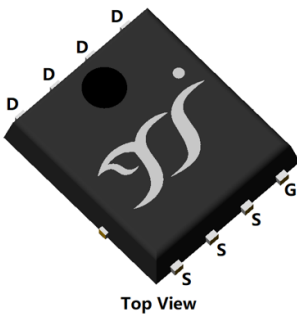
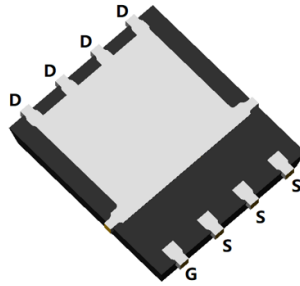


P-Channel Enhancement Mode Field Effect Transistor

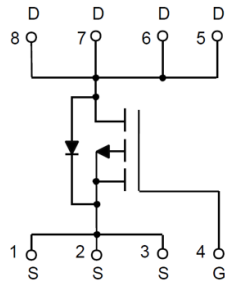


Top View



Bottom View

PDFN5060-8L



Product Summary

- V_{DS} -100V
- I_D -15A
- $R_{DS(ON)}$ (at $V_{GS}=-10V$) <110 mohm
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) <120 mohm
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 3
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- DC-DC Converters
- Power management functions

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-100	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25^\circ\text{C}$	I_D	-3	A
	$T_A=100^\circ\text{C}$		-2	
	$T_C=25^\circ\text{C}$		-15	
	$T_C=100^\circ\text{C}$		-9.6	
Pulsed Drain Current ^A		I_{DM}	-30	A
Avalanche energy ^B		EAS	64	mJ
Total Power Dissipation ^C	$T_A=25^\circ\text{C}$	P_D	2.5	W
	$T_A=100^\circ\text{C}$		1	
	$T_C=25^\circ\text{C}$		60	
	$T_C=100^\circ\text{C}$		24	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	$t \leq 10\text{S}$	$R_{\theta JA}$	15	20	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Ambient ^D	Steady-State		40	50	
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	1.7	2.1	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG15GP10A	F1	YJG15GP10A	5000	10000	100000	13" reel



YJG15GP10A

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =-250μA	-100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V	T _J =25°C		-1	μA
			T _J =55°C		-5	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =-250μA	-1.0	-1.8	-2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -10V, I _D =-15A		83	110	mΩ
		V _{GS} = -4.5V, I _D =-7A		95	120	
Diode Forward Voltage	V _{SD}	I _S =-15A, V _{GS} =0V			-1.3	V
Gate resistance	R _G	f=1MHz, Open drain	-	10	-	Ω
Maximum Body-Diode Continuous Current	I _S				-15	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =-50V, V _{GS} =0V, f=1MHZ		1051		pF
Output Capacitance	C _{oss}			119		
Reverse Transfer Capacitance	C _{rss}			25		
Switching Parameters						
Total Gate Charge	Q _{g(-10V)}	V _{GS} =-10V, V _{DS} =-50V, I _D =-5A		20.1		nC
Total Gate Charge	Q _{g(-4.5V)}			9.7		
Gate-Source Charge	Q _{gs}			3.9		
Gate-Drain Charge	Q _{gd}			4.3		
Reverse Recovery Charge	Q _{rr}	I _F =-5A, di/dt=100A/us		140		nC
Reverse Recovery Time	t _{rr}			80		
Turn-on Delay Time	t _{D(on)}	V _{GS} =-10V, V _{DD} =-50V, I _{DS} =-5A R _{GEN} =6Ω		10		ns
Turn-on Rise Time	t _r			30		
Turn-off Delay Time	t _{D(off)}			77		
Turn-off fall Time	t _f			81		

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T_J=25°C, V_{DD}=-50V, V_G=-10V, R_G=25Ω, L=0.5mH, I_{AS}=-16A.

C. Pd is based on max. junction temperature, using junction-case thermal resistance.

D. The value of RθJA is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with TA =25° C. The Power dissipation PDSM is based on RθJA ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.



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■ Typical Performance Characteristics

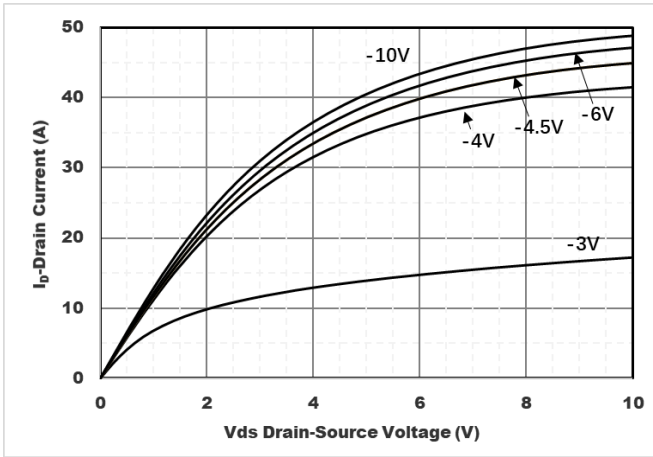


Figure1. Output Characteristics

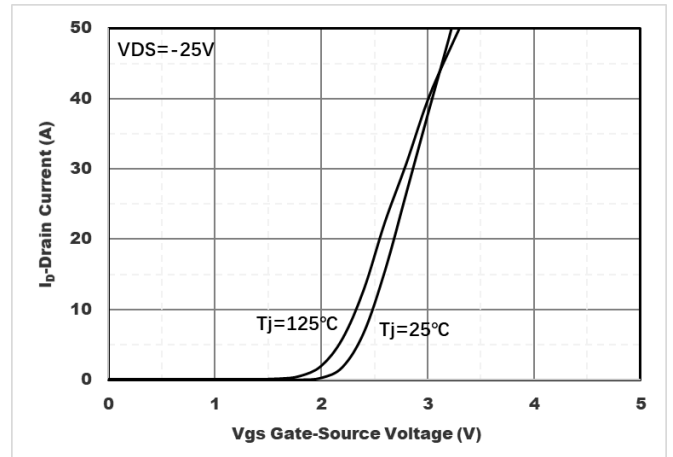


Figure2. Transfer Characteristics

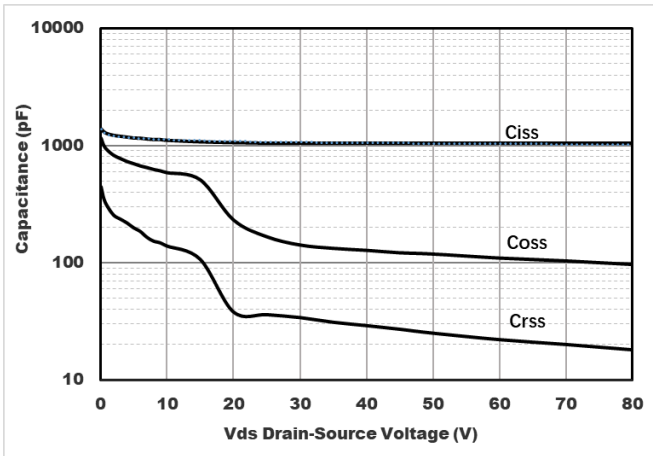


Figure3. Capacitance Characteristics

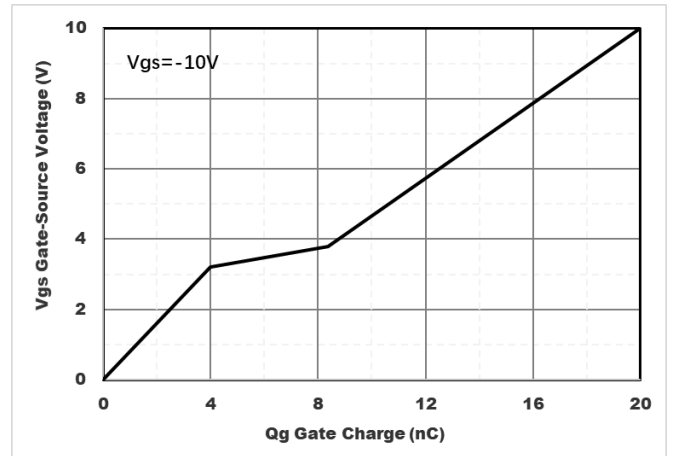


Figure4. Gate Charge

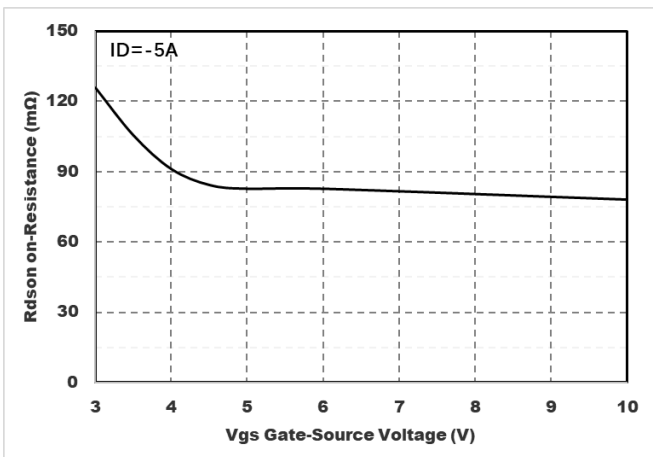


Figure5. : On-Resistance vs. Gate to Source Voltage

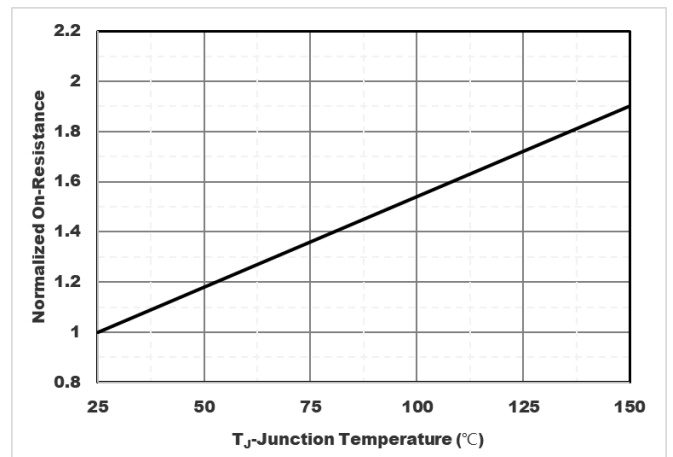


Figure6. Normalized On-Resistance



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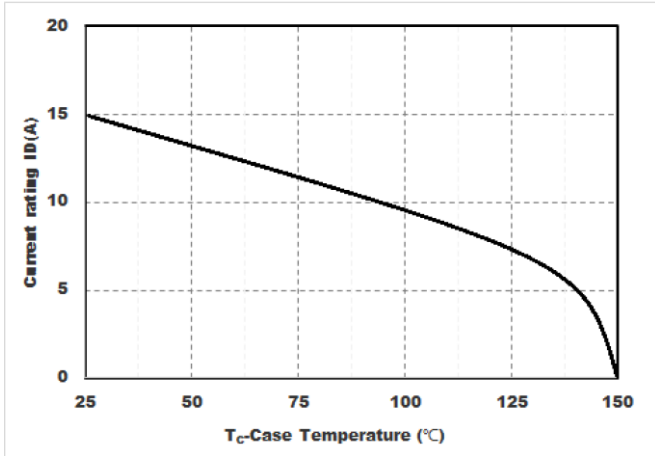


Figure7. Drain current

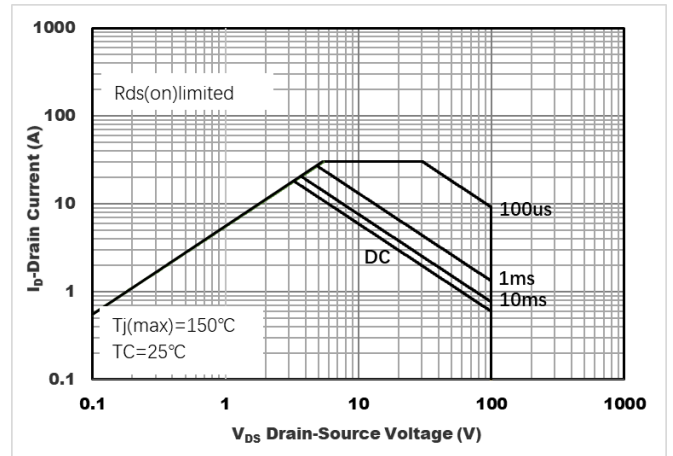


Figure8.Safe Operation Area

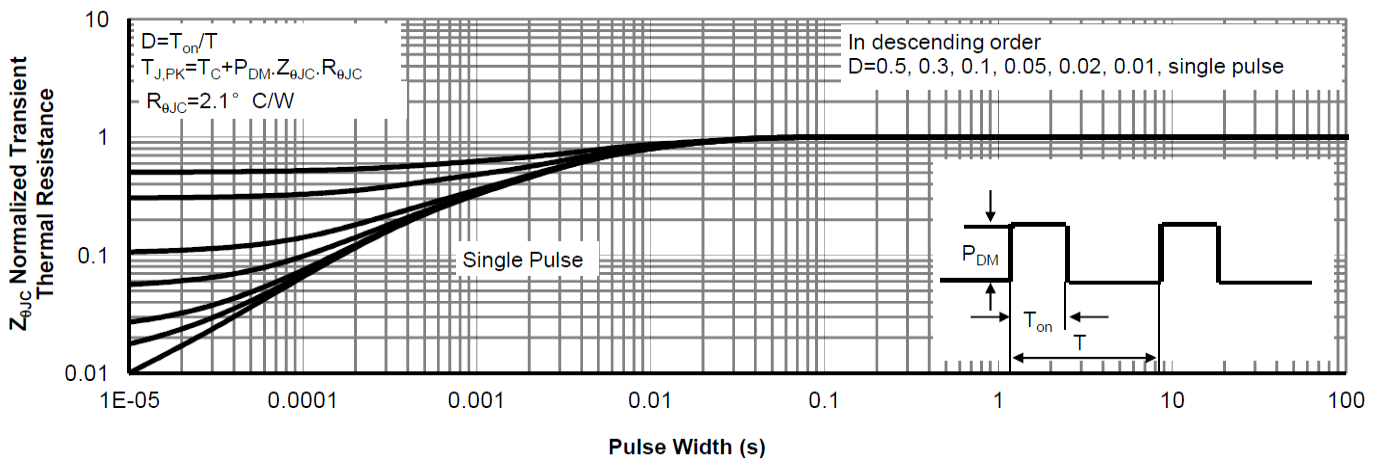
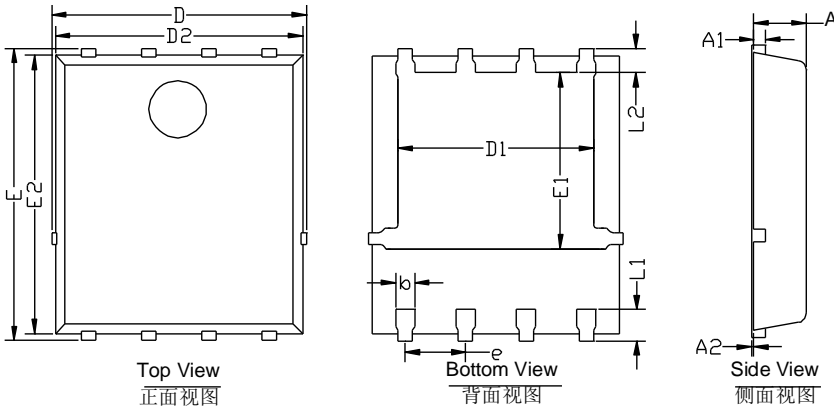


Figure9.Normalized Maximum Transient thermal impedance

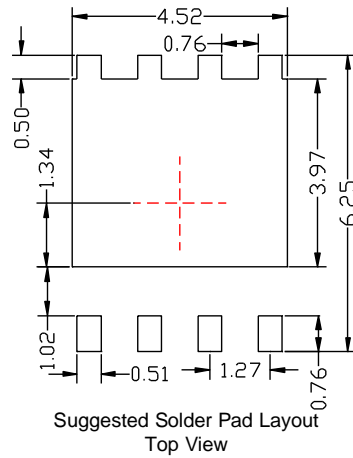


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■ PDFN5060-8L Package Information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.10 mm.
 3. The pad layout is for reference purposes only.



YJG15GP10A

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